

FRED

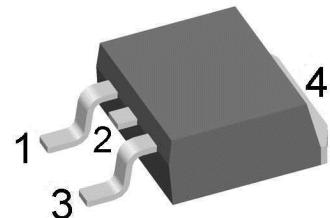
V_{RRM} = 600 V
 I_{FAV} = 20 A
 t_{rr} = 35 ns

Fast Recovery Epitaxial Diode Single Diode

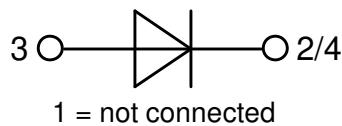
Part number

DSEI19-06AS

Marking on Product: DSEI19-06AS



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-263 (D2Pak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

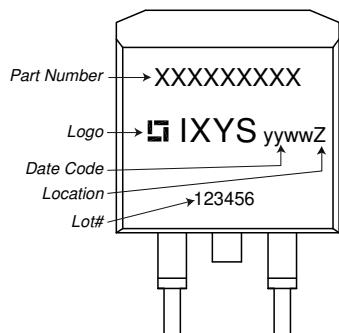
Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

Fast Diode

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^\circ\text{C}$			600	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^\circ\text{C}$			600	V
I_R	reverse current, drain current	$V_R = 600 \text{ V}$ $V_R = 480 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		50 3	μA mA
V_F	forward voltage drop	$I_F = 15 \text{ A}$ $I_F = 30 \text{ A}$ $I_F = 15 \text{ A}$ $I_F = 30 \text{ A}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 150^\circ\text{C}$		1.67 1.87 1.51 1.79	V V
I_{FAV}	average forward current	$T_C = 90^\circ\text{C}$ rectangular $d = 0.5$	$T_{VJ} = 150^\circ\text{C}$		20	A
V_{F0} r_F	threshold voltage slope resistance } for power loss calculation only		$T_{VJ} = 150^\circ\text{C}$		1.30 15.4	V $\text{m}\Omega$
R_{thJC}	thermal resistance junction to case				1.6	K/W
R_{thCH}	thermal resistance case to heatsink			0.25		K/W
P_{tot}	total power dissipation		$T_C = 25^\circ\text{C}$		62	W
I_{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}; V_R = 0 \text{ V}$	$T_{VJ} = 45^\circ\text{C}$		100	A
C_J	junction capacitance	$V_R = 600 \text{ V}$ $f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ\text{C}$		10	pF
I_{RM}	max. reverse recovery current		$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 100^\circ\text{C}$		2.5 4	A A
t_{rr}	reverse recovery time	$I_F = 14 \text{ A}; V_R = 350 \text{ V}$ $-di_F/dt = 100 \text{ A}/\mu\text{s}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 100^\circ\text{C}$		90 150	ns ns

Package TO-263 (D2Pak)

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
I_{RMS}	RMS current	per terminal			25	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				1.5		g
F_c	mounting force with clip		20		60	N

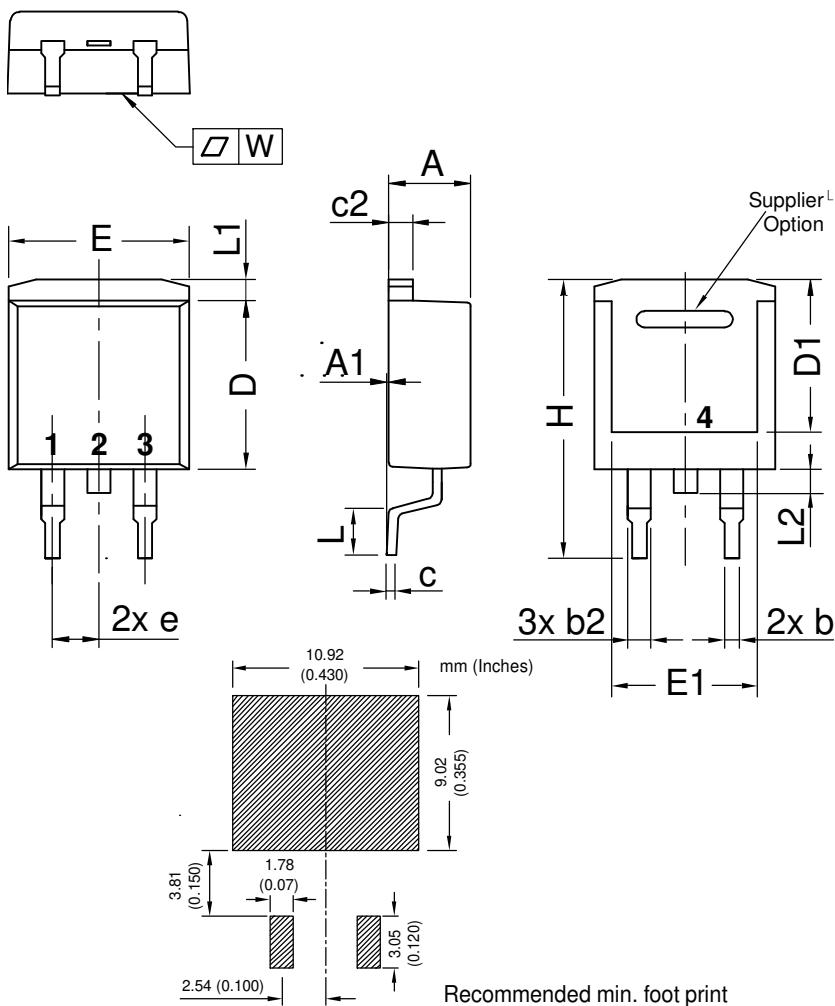
Product Marking


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEI19-06AS-TRL	DSEI19-06AS	Tape & Reel	800	499455
Alternative	DSEI19-06AS-TUB	DSEI19-06AS	Tube	50	464570

Equivalent Circuits for Simulation
* on die level
 $T_{VJ} = 150^\circ\text{C}$

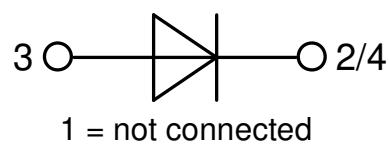
	Fast Diode	
$V_{0\max}$	threshold voltage	1.3
$R_{0\max}$	slope resistance *	12.3

Outlines TO-263 (D2Pak)



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.06	4.83	0.160	0.190
A1	typ. 0.10		typ. 0.004	
A2	2.41		0.095	
b	0.51	0.99	0.020	0.039
b2	1.14	1.40	0.045	0.055
c	0.40	0.74	0.016	0.029
c2	1.14	1.40	0.045	0.055
D	8.38	9.40	0.330	0.370
D1	8.00	8.89	0.315	0.350
D2	2.5		0.098	
E	9.65	10.41	0.380	0.410
E1	6.22	8.50	0.245	0.335
e	2,54 BSC		0,100 BSC	
e1	4.28		0.169	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.02	1.68	0.040	0.066
W	typ. 0.02	0.040	typ. 0.0008	0.002

All dimensions conform with
and/or within JEDEC standard.



Fast Diode

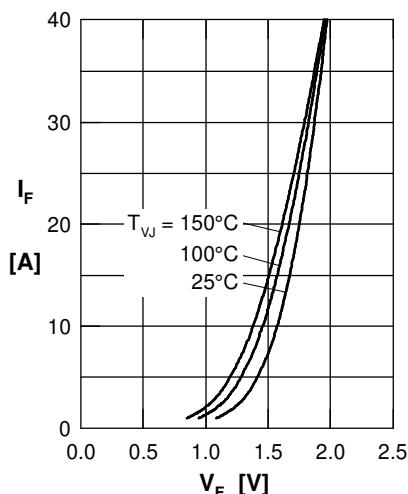


Fig. 1 Forward current I_F versus
max. forward voltage drop V_F

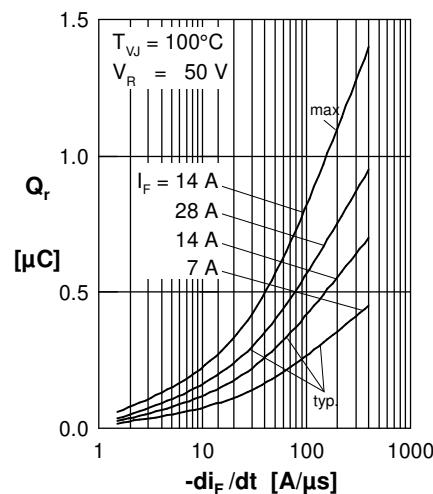


Fig. 2 Typ. reverse recov. charge
 Q_r versus $-di_F/dt$

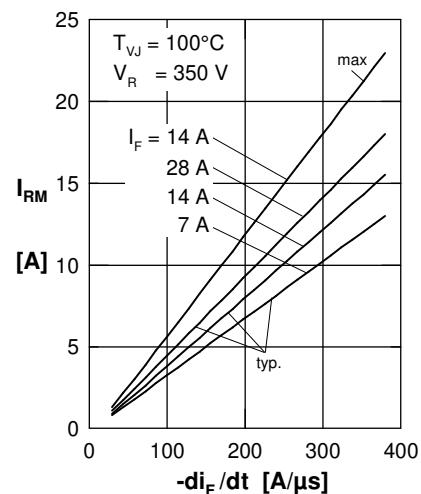


Fig. 3 Typ. peak reverse current
 I_{RM} versus $-di_F/dt$

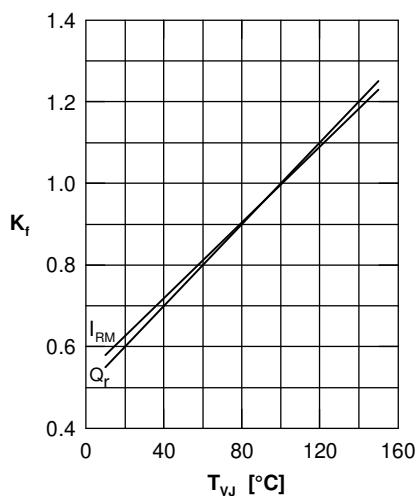


Fig. 4 Dynamic parameters
 Q_r , I_{RM} versus T_{VJ}

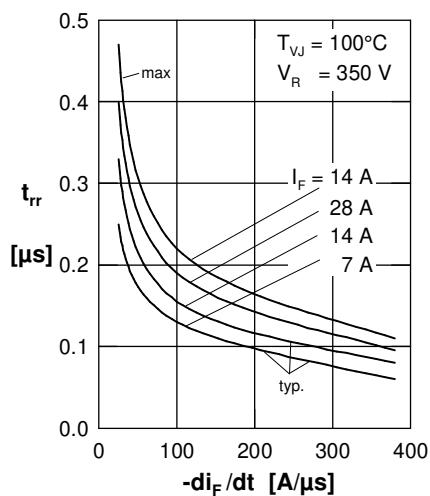


Fig. 5 Typ. recovery time
 t_{rr} versus $-di_F/dt$

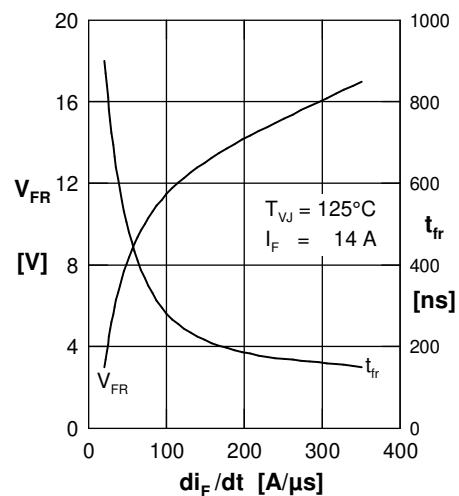


Fig. 6 Typ. peak forward voltage
 V_{FR} and t_{fr} versus di_F/dt

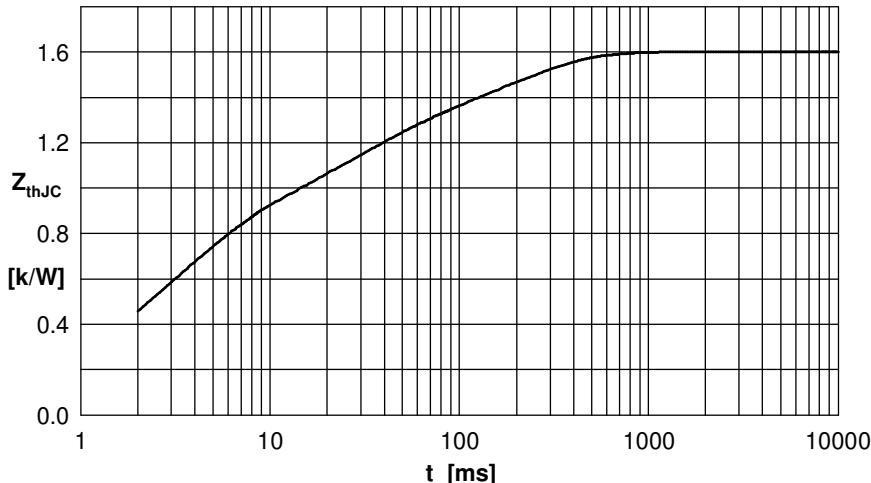


Fig. 7 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.100	0.001
2	0.020	0.010
3	0.400	0.180
4	0.400	0.024
5	0.680	0.003

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Schottky Diodes & Rectifiers category:

Click to view products by IXYS manufacturer:

Other Similar products are found below :

[MA4E2039](#) [D1FH3-5063](#) [MBR0530L-TP](#) [MBR10100CT-BP](#) [MBR1545CT](#) [MMBD301M3T5G](#) [RB160M-50TR](#) [RB551V-30](#)
[BAS16E6433HTMA1](#) [BAT 54-02LRH E6327](#) [NSR05F40QNXT5G](#) [NTE555](#) [JANS1N6640](#) [SB07-03C-TB-H](#) [SB1003M3-TL-W](#) [SK310-T](#)
[SK32A-LTP](#) [SK34B-TP](#) [SS3003CH-TL-E](#) [GA01SHT18](#) [CRS10I30A\(TE85L,QM](#) [MA4E2501L-1290](#) [MBRB30H30CT-1G](#) [SB007-03C-TB-](#)
[E](#) [SK32A-TP](#) [SK33B-TP](#) [SK38B-TP](#) [NRVBM120LT1G](#) [NTE505](#) [NTSB30U100CT-1G](#) [SS15E-TP](#) [VS-6CWQ10FNHM3](#) [ACDBA1100LR-](#)
[HF](#) [ACDBA1200-HF](#) [ACDBA140-HF](#) [ACDBA2100-HF](#) [ACDBA3100-HF](#) [CDBQC0530L-HF](#) [CDBQC0240LR-HF](#) [ACDBA260LR-HF](#)
[ACDBA1100-HF](#) [SK310B-TP](#) [MA4E2502L-1246](#) [MA4E2502H-1246](#) [NRVBM120ET1G](#) [NSR01L30MXT5G](#) [NTE573](#) [NTE6081](#) [SB560](#)
[PMAD1108-LF](#)